



CORNERSTONE Device Dimensions for 500 nm SOI Platform

Rib waveguide etch depth = 300 nm

Grating etch depth = 160 nm



TE mode
 $\lambda = 1550 \text{ nm}$

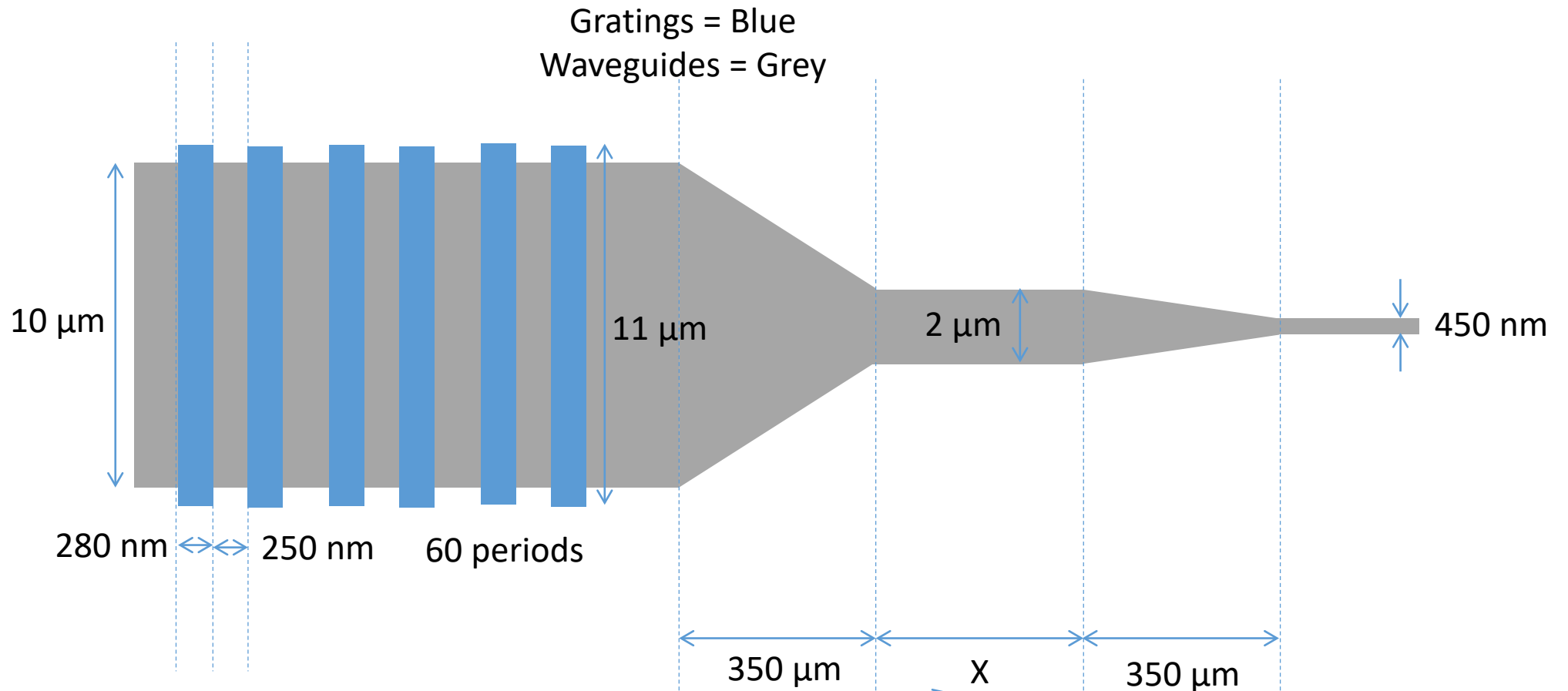
Rib waveguide etch depth = 300 nm
Grating etch depth = 160 nm



TE single mode waveguides and bends

Property	Wavelength = 1550 nm
<u>Rib waveguides</u>	
Maximum single mode waveguide width (nm)	450
Minimum bend radius (width = 450 nm) (μm)	25

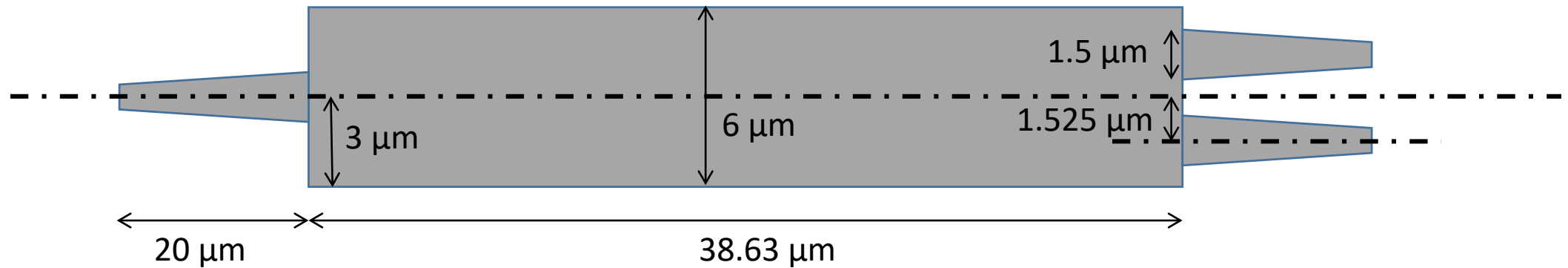
TE grating coupler (etch depth = 160 nm)



Use waveguide of width X for low loss routing to devices if required

*Add rib protect layer in GDS file

*Prototype device that has not yet been tested



*Add rib protect layer in GDS file